

LUMPED ELEMENTS AND ITS EXISTENCE IN QUASI LUMPED ELEMENT RESONATOR ANTENNA

Abstract

In this paper, the Quasi Lumped Element Resonator Antenna is reviewed. It is composed of Lumped elements. Lumped Elements are passive components whose size across any dimensions should be small to make it a lumped element. The various researches that have been done to come about the various types of basic building blocks of the lumped element are staged in this write up. This review is towards accomplishing the derivation of the component elements used in the design of the Quasi Lumped Element Resonator Antenna. These elements are the interdigital capacitor, inductor and pad capacitors. The pertinent formulae for determining each one of them were all expressed in this review. The formula for calculating the resonance frequency of the Quasi Lumped Element Resonator Antenna was expressed in this review. The equivalent circuit model for the lumped elements were all reviewed and presented. This review brings about how the lumped elements are involved in the design of the Quasi Lumped Element Resonator Antenna.

Keywords- Lumped Element, Frequency, Quasi Lumped Element Resonator Antenna.

1.0 Introduction

Devices capable of radiating and receiving radio waves are known as antennas (Balanis, 2016). They are at the interface between free space and the guiding device. The guiding device is the transmission line through which an electrical signal travels before conversion into electromagnetic waves or radiation energy for transmission or transportation through free space.

Antennas are of a variety of types with each having different shapes. These include wire antenna, microstrip patch antenna, reflector antenna, array antenna, lens antenna, aperture antenna and Quasi Lumped Element Resonator Antenna. Quasi Lumped Element Resonator Antenna is an exception in its design behavior because its resonance frequency depends on some lumped element components. These makes it to have a high degree of freedom and flexibility.

Quasi lumped Element Resonator antenna is made up of lumped capacitor, lumped inductors (Olokede & Adamariko, 2015). By understanding the behavior of these lumped elements, the antenna behavior can be predicted. Lumped elements are passive components in microwave circuits whose size across any dimension is much smaller than the operating wavelength to ensure that there is no appreciable phase shift between the input and output terminals (Olokede, 2015). When using lumped elements at RF and microwave frequencies, the maximum dimensions for these components should be about $\lambda/20$, where λ is the guide wavelength (Olokede *et. al*, 2015). Lumped elements circuits can be divided as shown in Figure 1.0

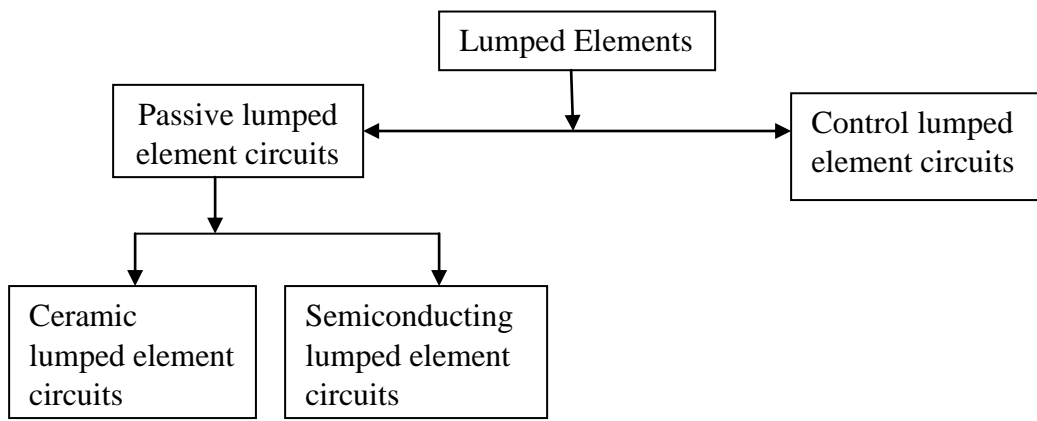


Figure 1.0: Division of Lumped Elements in Microwave Circuit

The lumped element circuit is a ceramic lumped element circuit if thick film printed inductors and discrete capacitors are used, while it is a semiconductor lumped element circuits when High Temperature Semiconductors (HTSs) are used in its design instead of the Duroid Microwave substrate (Bahl, 2003).

Figure 1.1 shows the basic building blocks from which lumped elements are derived and some commonly used components

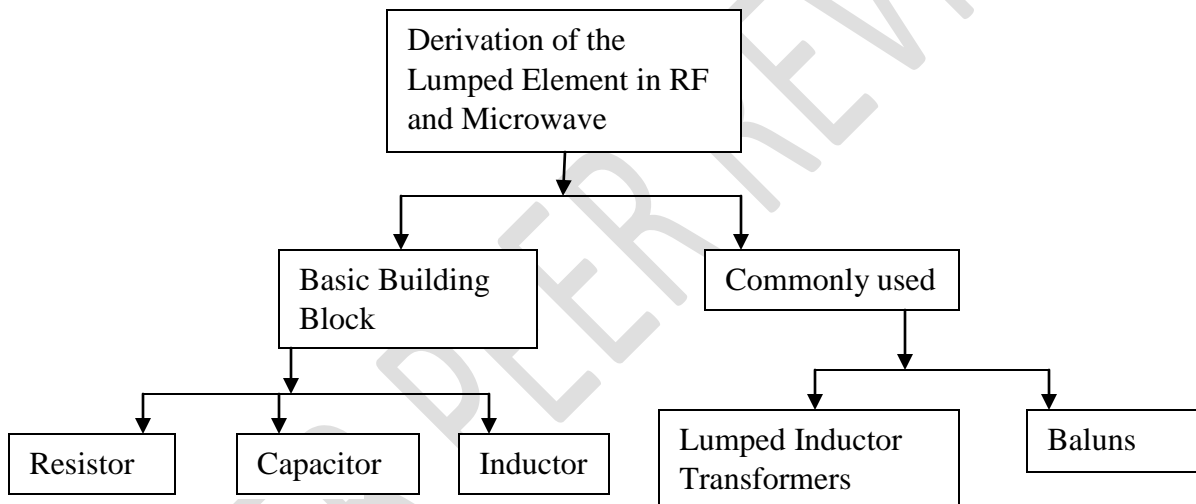


Figure 1.1: Lumped Elements in RF and Microwave Circuits

From Figure 1.1, the basic building blocks of lumped element in RF and microwave circuits are the resistor, capacitor and inductor. While the commonly used are Lumped inductor transformers and baluns (Bahl, 2003)

1.1 Basic Circuit Elements of the Lumped Element

In this subsection a brief review of the basic mathematical relationship between the terminal voltage and current across each of the circuit elements is described.

This review is necessary as it serves as the background for this study. Consider that these elements (Inductor, L ; Capacitor C ; and Resistor R) as shown in Figure 1.2 are ideal (pure and linear).

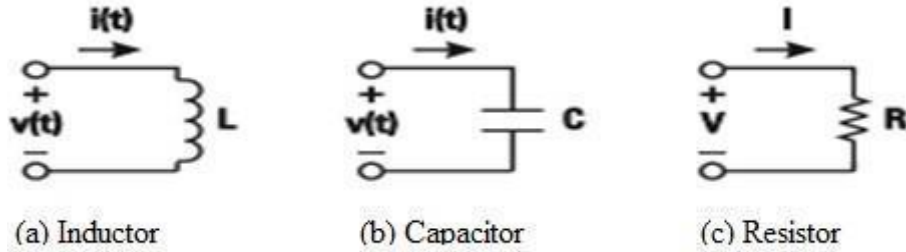


Figure 1.2: Two-Terminal Voltage and Current Representation of Lumped Elements (Bahl, 2003).

In Figure 1.3 (a), an ideal inductor of inductance L is depicted, $i(t)$ is the time-varying current passed through the inductor of inductance L and $v(t)$ is voltage across its terminals. The inductor stores or releases magnetic energy W_m and does not store electric energy. The inductor does not dissipate any power and the phase of the time-varying current $i(t)$ lags the phase of the voltage $v(t)$ across its terminals. This is stated mathematically as follow (Bahl, 2003):

$$V_{(t)} = L \frac{di_{(t)}}{dt} \quad (1.0)$$

$$V = j\omega L i \quad (1.1)$$

$$I_{(t)} = \left(\frac{1}{L}\right) \int V_{(t)} dt \quad (1.2)$$

$$I = \frac{v}{j\omega L} \quad (1.3)$$

$$W_m = \frac{1}{2} * L i_0^2 \quad (1.4)$$

In equations (1.0) to (1.4), the time dependence is assumed to be $e^{j\omega t}$ and i_0 is the root mean square (rms) value of the current.

Figure 1.3(b) depicts an ideal capacitor of capacitance C . $i(t)$ is the time-varying current passed through the capacitor C and $v(t)$ is voltage across its terminals. The capacitor of capacitance C in Figure 1.3(b) stored or released energy but only of electric type. The capacitor does not dissipate any power and the phase of the time-varying current $i(t)$ leads the phase of the voltage $v(t)$ across its terminals. This is stated mathematically as follows (Bahl, 2003):

$$I_{(t)} = C * \frac{dv_{(t)}}{dt} \quad (1.5)$$

$$I = j\omega c v \quad (1.6)$$

$$V_{(t)} = \frac{1}{c} * \int i_{(t)} dt \quad (1.7)$$

$$W_e = C V_0^2 \quad (1.8)$$

where

v_0 is the rms value of the voltage.

105 A linear resistor is a lossy component whose dimensions are much less than the operating
106 wavelength. In this component, the voltage applied to its terminals and the current passing
107 through the resistor are in phase and the incident power is completely dissipated. Let V and I be
108 the rms voltage and current across a resistor of value R, therefore, Ohm's law is stated as:

$$109 \quad V=RI \quad (1.9)$$

110 And the power dissipated is given as:

$$111 \quad P=IV \quad (1.10)$$

112 2.0 Lumped Element Modeling

113 In order to use lumped elements correctly, the idea about how the lumped elements are modeled
114 should be known. At RF and microwave frequencies, to model this lumped elements, they are
115 realized based on a maximum dimension of one-twentieth of a wavelength, which is based on a
116 small section of a microstrip line. The design is done by selecting a suitable length of each
117 section. The lumped capacitor can be realized by using an open circuited ($Z_L = \infty$) microstrip
118 sections and a lumped inductor is realizable using a short circuited ($Z_L = 0$) microstrip section.
119 Thus, a small section of the short circuited transmission line behaves as a lumped inductor in
120 series with a resistance R (Rafiee, 2015). It is a lumped inductor if the value of the resistance is
121 very small, but where the conductor used in designing the lumped element is Nicr (gold), the
122 value of the resistance is high and the lumped element is resistive. The proportional value of the
123 resistance, inductance, and capacitance components depend on the use of the lumped element. If
124 the short circuited line has zero resistance in series with the inductor. The short circuited
125 microstrip line then behaves as an inductor, otherwise when the resistance is very high, as in the
126 case of an inductor in series with a high resistance, for example when Nicr (gold) is used as the
127 conductor, the microstrip section behaves as a resistor (Olokede, 2013). These small sections are
128 called quasi-lumped elements at High Frequency (HF) since the sections are used to replace the
129 actual lumped elements (Rafiee, 2015). An ideal lumped element is not realizable at lower
130 microwave frequencies because of the associated parasitic reactance caused by fringing fields
131 (Olokede, 2019). Each component has associated electric and magnetic fields and finite
132 dissipative loss at RF and microwave frequencies (Rafiee, 2015).

133 Thus, each component stores or releases magnetic and electric energies across them and their
134 resistance dissipates power (Bahl, 2003).

135 Basic circuit elements (resistance, inductance, and capacitance) with their associated parasitics
136 are included in Lumped-Element Equivalent Circuit (LEEC) models. The relative measure of the
137 C, L, and R components in the LEEC depend on the necessary use of the LE. The LEEC model
138 are used to describe the electrical behavior of the components. For a Computer Aided Design
139 (CAD) of MICs and MMICs (Leferink, 1995), there is need for a model that is comprehensive.
140 This constitutes the effect of fringing fields, ground plane, conductor thickness, substrate
141 material and thickness, associated mounting techniques and applications needed, non-uniform
142 current distribution. Note that the non-uniform current distribution is caused either by the field
143 produced by the current itself (skin-effect), the return current (proximity effect) or the current
144 induced in the primary conductor (caused by the field of the return current on the LEs) (Rafiee,
145 2015).

146 For an accurate modelling of the lumped element, an equivalent circuit representation of the
 147 lumped element LEEC together with its parasitics and the corresponding frequency depending
 148 characteristics are necessary. Thus, a LEEC model includes the required circuit elements to
 149 completely demonstrate its behaviour, particularly its possible resonances. The models can be
 150 completed using mathematical, CAD simulation and measurement based methods. The
 151 component size should be made much smaller as a lumped element is realizable at a dimension
 152 of the wavelength/20 (Bahl, 2003).

153 2.1 Equivalent Circuit Modelling of Lumped Inductor

154 Modelling in terms of electrical circuits and numerical equations for each of the components
 155 (interdigital capacitor, pad capacitor, straight line inductor or inductor) of lumped element is
 156 indispensable for a precise quasi lumped element modeling. Thus, as early as 1943, models were
 157 developed for LEs. These models were based on analytical semi empirical equations. Terman, (1943)
 158 was able to publish an expression for the inductance of a thin metallic straight line. The expression
 159 was subsequently improved by Caulton *et al.*, (1968), by adding the metallization thickness.
 160 Wheeler, (1928) published an approximate formula for the inductance of a circular spiral inductor
 161 with reasonably good accuracy at lower microwave frequencies. This formula has been tremendously
 162 used in the design of microwave lumped circuits as stated in equation (2.1). Grover, (2004) discussed
 163 inductance calculations for several geometries. In a lot of the cases, two methods have been used in
 164 the theoretical modeling of microstrip inductors for MICs. The first method is the lumped-element
 165 approach and the second method is the coupled-line approach. The lumped–element approach uses
 166 frequency independent formulae for free-space inductance with ground plane effects. These
 167 frequency-independent formulae are useful only when the total length of the inductor is a little
 168 fraction of the operating wavelength and when inter-turn capacitance can be ignored. In the coupled-
 169 line approach, the multi-conductor coupled microstrip lines are used to analyze an inductor. The later
 170 technique predicts performance reasonably well for up to two turns and frequencies up to 18 GHz
 171 (Bahl, 2003).

172 3-D electromagnetic simulators can be used to determine the accurate characterization of inductors
 173 including the effects of radiation, surface waves, and not excluding the interaction between
 174 components on the performance of densely packed inductors in MMICs (Bahl, 2003).

175 One method that gives an accurate result for a model of lumped inductor is by measuring dc
 176 resistance and S-parameters. Although, they are limited to the device being measured, the equivalent
 177 circuit parameters are extracted from computer optimization and are correlated with the measured dc
 178 resistance and S-parameters data (one or two port data) and are valid up to 26 or 40 GHz depending
 179 on the application.

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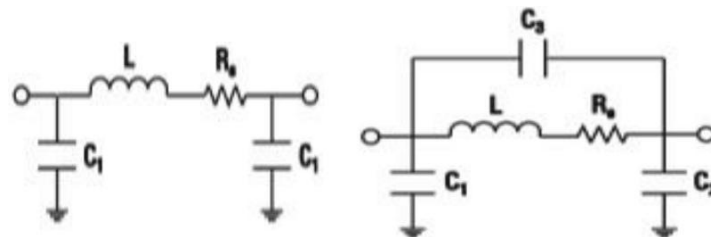
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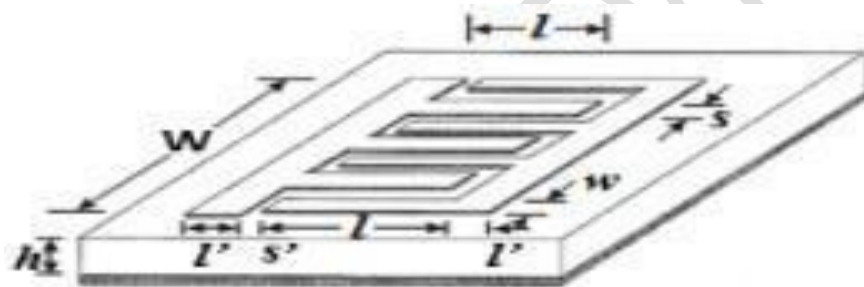
(a) Microstrip Section and Loop

(b) Coil

Figure 2.0: Equivalent Circuit Model for Lumped Inductor (Bahl, 2003)

187 **2.2 Equivalent Circuit Modelling of Lumped Capacitor (Interdigital Capacitor)**

188 An interdigital capacitor is a multi finger periodic structure. This multi finger structure consists
189 of fingers that are equally spaced with gaps of equal width in between them. The gaps are very
190 narrow and the capacitance occurs across the interdigital fingers. The gaps are folded to form a
191 long length and use a small amount of space and consequently its attendant relevance has a
192 lumped element. The interdigital capacitor is larger than an overlay capacitor (Bahl, 2003). The
193 structure for an interdigital capacitor is shown in Figure 2.1. The capacitance of the interdigital
194 capacitor can be increased by increasing the number of fingers, putting a thin layer high
195 dielectric constant material between the conductors and the substrate, using an overlay dielectric.
196 This methods increase the interdigital capacitance and the overlay dielectric also acts as a
197 protective shield after fabrication. Interdigital capacitors can be employed with Monolithic
198 Microwave Integrated Circuit (MMIC) designs and Microwave Integrated Circuit (MIC) designs
199 at higher frequency as they can be used instead of the discrete circuit designs. A necessary
200 design consideration for the interdigital capacitor is to keep its size very small in comparison
201 with a wavelength in order for it to possess the characteristics of a lumped element.



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208 Figure 2.1: Interdigital Capacitor (Bahl, 2003)

209 To analyze interdigital capacitors, there are four famous techniques. The techniques are
210 approximate analysis, J-inverter network equivalent representation, full wave analysis, and
211 measurement based model. Due to the relevance, comprehensibility, and accuracy (Bahl, 2003)
212 of the first method, it is utilized in this work.

213 The analysis for the interdigital capacitor using the approximate analysis was based on lossless
214 microstrip coupled line theory (Alley, 1970) and the loss effects were added to make the lossy
215 coupled microstrip lines by representing it with mathematical calculations (Hobdell, 1979).

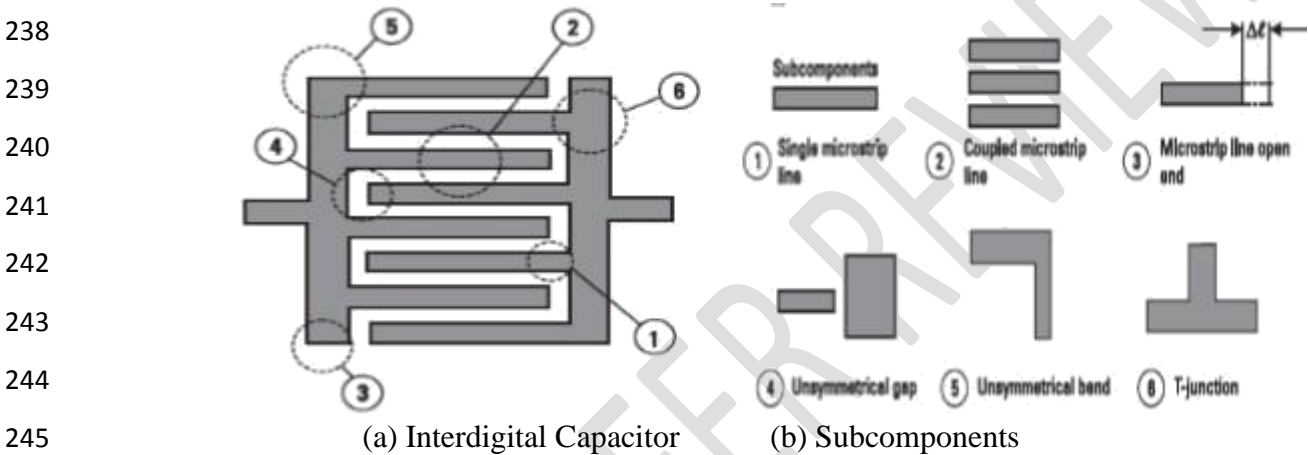
216 About four years since Hobdel, (1979) introduced the mathematical calculations; the effect of
217 metallization was added onto the two factors: capacitance and the Q factor (Esfandiari *et al.*,
218 1983). On the other hand, Alley's theory did not consider different positions of fingers with
219 admittance calculation of parallel shunt fingers.

220 Also, the phase shift along the main line was not considered which was distinct in interdigital
221 capacitor with high number of fingers. In addition, the effects of gaps, bends, the T-junctions,
222 the open end of microstrip line and discontinuity of the structure were not taken into account. A
223 more accurate characterization of these capacitors could be performed if the capacitor geometry
224 was divided into basic microstrip sections and subsections (Pettenpaul *et al.*,
225 1988).ThePattenpaul *et al.* (1988) publication was based on (Wolff and Kibuuka, 1984) theory.
226 This model could therefore be said to provide better accuracy than the previously reported

227 analyses. Nonetheless, this method can at best be regarded as an approximate solution rather
 228 than an explicit or exact. This is due to several assumptions in the grouping of sub-sections and
 229 as such, could not account for interaction effects between the microstrip sections. This microstrip
 230 sections and subsections are:

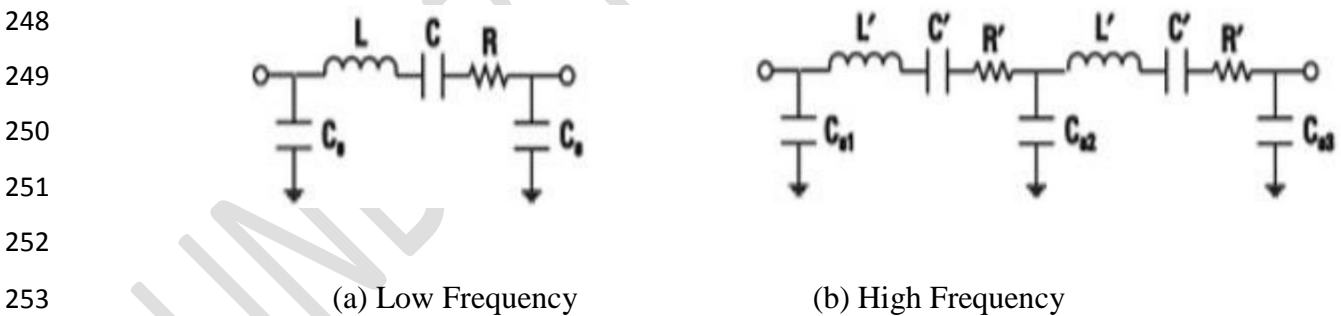
- 231 1. The single microstrip line.
- 232 2. The coupled microstrip lines.
- 233 3. The microstrip open-end discontinuity.
- 234 4. The microstrip unsymmetrical gap.
- 235 5. The unsymmetrical microstrip 90° bend.
- 236 6. The microstrip T-junction discontinuities.

237 These components are shown in Figure 2.2.



246 Figure 2.2: Lumped Capacitor (Bahl, 2003)

247 The value of the interdigital capacitor can be obtained using equation (2.2)



254 Figure 2.3: Lumped Element Equivalent Circuit Models of Interdigital

255 Capacitor (Bahl, 2003).

256 **Numerical Approach:** Although, the equivalent circuit models for the interdigital capacitor and
 257 inductor can be used to model them, they were explained as not exact and explicit. Equations
 258 (2.1) through (2.6) can be used to determine the dimensions and resonance frequency required
 259 for a particular design of the quasi lumped element resonator antenna. However, these are just
 260 estimates, especially at high frequencies, for designing the circuit and are not accurate. By using
 261 numerical methods employed via electromagnetic (EM) simulators, the antenna can be simulated

262 efficiently and additional features in the layout of the design can be adjusted, it can meet with
263 different configurations (2-D or 3-D) and it is versatile.

264 The simulators put into consideration other constraints such as junction discontinuities, substrate
265 effects (thickness and dielectric constant). The most common field solver technique employed
266 with planar structures is the Method of Moments (MoM) while for 3-D structures, it is more of
267 the Finite Element Method (FEM). Both of these techniques function with EM analysis in the
268 frequency domain. FEM is used when a more complex design is involved than with MoM and it
269 also uses a lot of computation time and requires much more memory. EM analysis in the time
270 domain also exists, example of these techniques are Transmission Line Matrix (TLM) method
271 and the Finite Difference Time-Domain (FDTD) method.

272 From the litteratures, it is now known that the inductor and capacitors are given by

273 i. **Inductor:** The inductor is a single, narrow and straight conductor, which is located at the
274 centre finger and shorted across the interdigital capacitor. It is presented in parallel with the
275 interdigital capacitor in the circuit diagram for the quasi lumped element resonator antenna
276 showed in Figure2.1. The magnitude of the inductor can be increased by using a meander line.
277 The equation for determining the value of the inductance of the inductor is given as (Avenhaus,
278 1996) (Bello *et. al*, 2018) :

$$279 \quad L = 200 * 10^{-9} I_L \left(\ln \frac{2 * I_L}{w_1 + t} + 0.50049 + \frac{w_1}{3 * I_L} \right) \quad (2.1)$$

280 where:

281 L is the inductance of the interdigital capacitor,

282 I_L is the inductor length

283 W_1 is the inductor width

284 t is the thickness of the resonator

285 ii. **Interdigital capacitor:** It is a structure containing a multi periodic arrangement of
286 conductors with equal spacing in between in the form of a multi finger like periodic pattern. This
287 structure is associated with the capacitance used by the quasi lumped element resonator antenna. The
288 interdigital capacitor is usually in parallel with the inductor in the quasi lumped element resonator
289 antenna equivalent circuit (Ain *et al.*, 2013). The approximate value for the interdigital capacitor can
290 be calculated (Huang *et al.*, 1999) as follows:

$$291 \quad C = e_o * \frac{e_r + 1}{2} * (N - \Delta) * C_L \quad (2.2)$$

292 where:

293 C is the capacitance of the interdigital capacitor

294 e_o is the permittivity of free spaced

295 e_r is the dielectric constant of the substrate

296 N is the number of fingers

297 Δ is the correction factor

298 C_L is the overlapping length of the interdigital capacitor fingers.

299 iii. **Pad Capacitors:** The pad capacitors are two and are at both sides of the resonator. They
 300 are represented with C_{p1} and C_{p2} as shown on Figure 2.1(b). They act as capacitors to the
 301 ground and can be adjusted to tune the resonant frequency of the resonator. The respective
 302 values of C_{p1} and C_{p2} do not depend on the number of interdigital fingers or the size of the
 303 fingers. This is because the location of the ground plane can be adjusted to minimize their
 304 effects. The two pad capacitors are of the same value and their value can be estimated (Bogatin,
 305 1988) as:

$$306 \quad C_p = \left[\frac{2.85 * e_{eff}}{\ln\left(1 + \frac{1}{2} * \left(\frac{8 * \square}{w_{eff}}\right) * \left(\frac{8 * \square}{w_{eff}}\right) + \sqrt{\left(\frac{8 * \square}{w_{eff}}\right)^2 + \pi^2}\right)} \right] * \left[\frac{l}{25.4 * 10^{-3}} \right] \quad (2.3)$$

307 where:

308 C_p is the pad capacitance

309 h is the thickness of the substrate

310 e_{eff} is the effective dielectric constant of the substrate

311 l is the length of the pad

312 w_{eff} is the effective corrected transmission line width

313 i. **Resonant frequency:** The resonant frequency of an antenna is the frequency at which
 314 electromagnetic waves can be transmitted or received by the antenna. The resonant frequency of
 315 the quasi lumped element resonator antenna is calculated using the following expression (Ain
 316 and Hassan, 2004)

$$317 \quad f = \frac{1}{2 * \pi * \sqrt{L * \frac{C_{p1} C_{p2}}{C_{p1} + C_{p2}} + C}} \quad (2.4)$$

318 where:

319 f is the resonant frequency of the antenna

320 L is the inductance of the inductor

321 C_{p1} , is the pad capacitance

322 C is the capacitance of the interdigital capacitor

323 The parameters e_{eff} and w_{eff} are expressed mathematically as:

$$324 \quad e_{eff} = \frac{e_r + 1}{2} + \frac{e_r - 1}{2} * \left(1 + 10 * \frac{\square}{w}\right)^{-\frac{1}{2}} \quad (2.5)$$

$$325 \quad w_{eff} = w + \left[\frac{4 * e}{\sqrt{\left(\frac{t}{\square}\right)^2 + \left(\frac{1}{\pi \left(\frac{w}{t} + 1.10\right)}\right)^2}} \right] \quad (2.6)$$

326 where:

327 w is the width of the pad
328 h is the height of the substrate
329 t is the thickness of the conductor
330 e is 2.713
331 w_{eff} is the effective corrected transmission line width
332 ϵ_r is the dielectric constant of the substrate

333 Given all this parameters, the Quasi lumped element resonator antenna can be designed

334 **Conclusion**

335 This paper presented Lumped Elements and its Existence in Quasi Lumped Element Resonator
336 Antenna. Lumped Elements was described and the formulas for describing those component
337 Lumped Element parts were extracted from literatures. The Quasi Lumped Element Resonator
338 Antenna is designed based on some lumped element component parts. Its resonant frequency is
339 not proportional to the length of the antenna but the constitution of the lumped elements.

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